

N-channel 80 V, 9.9 mΩ standard level MOSFET in LFPAK56 8 May 2013 Product data sheet

## 1. General description

Standard level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

## 3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	89	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	195	W
Static charact	eristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	7.3	9.9	mΩ
Dynamic char	acteristics			1		
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 64 V; Fig. 13; Fig. 14	-	14.4	-	nC

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BUK7Y9R9-80E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7Y9R9-80E	79E980

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

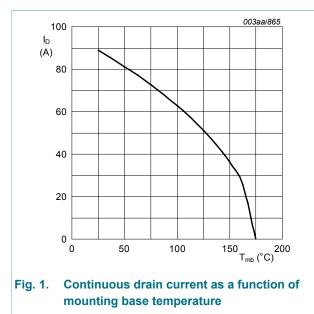
Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	89	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	63	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4	-	354	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	195	W
T <sub>stg</sub>	storage temperature		-55	175	°C

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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	89	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	354	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$    I_D = 89 \text{ A}; V_{sup} \le 80 \text{ V}; \text{ R}_{GS} = 50 \Omega; V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}; Fig. 3 $	[1][2]	-	106	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^\circ\text{C}.$ 

[2] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$ 

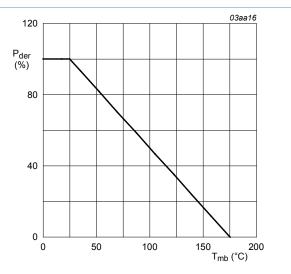
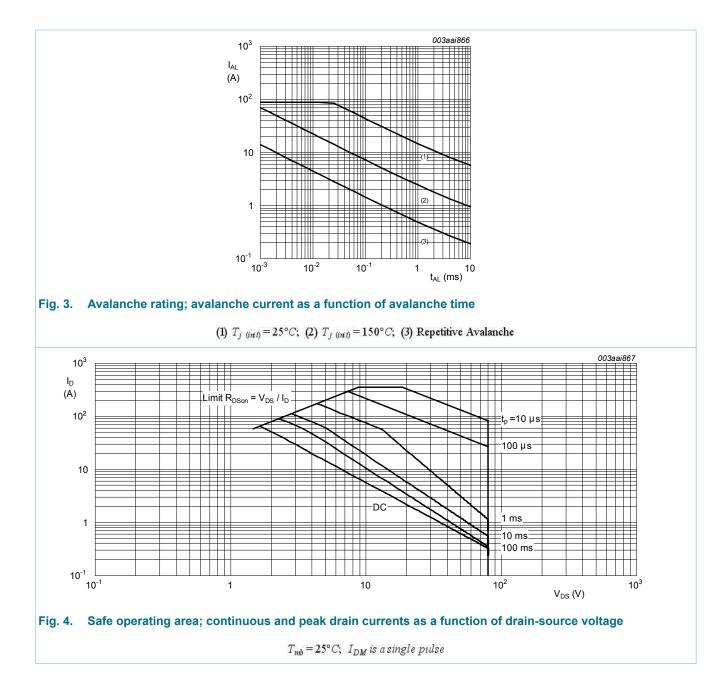


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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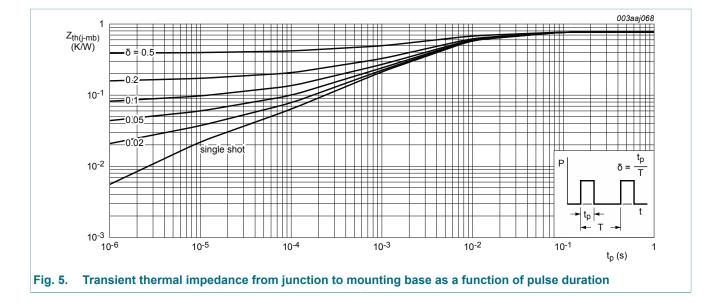
### N-channel 80 V, 9.9 m $\Omega$ standard level MOSFET in LFPAK56



## 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

### N-channel 80 V, 9.9 m $\Omega$ standard level MOSFET in LFPAK56



# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·	1			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	80	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	72	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9	1	-	-	V
I <sub>DSS</sub> drain leakage current	$V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.13	10	μA	
		$V_{DS}$ = 80 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub> gate leakage current	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	24.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	7.3	9.9	mΩ
Dynamic ch	naracteristics	· · · · · ·	1			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 64 V; $V_{GS}$ = 10 V;	-	51.6	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	14.1	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	14.4	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;		-	3200	4266	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	303	364	pF
C <sub>rss</sub>	reverse transfer capacitance			-	165	226	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 60 \text{ V}; \text{ R}_{L} = 2.4 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G(ext)} = 5 \Omega$		-	15	-	ns
t <sub>r</sub>	rise time			-	23	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	34	-	ns
t <sub>f</sub>	fall time			-	21	-	ns
Source-drai	n diode	1	I				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V;		-	35	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	52	-	nC

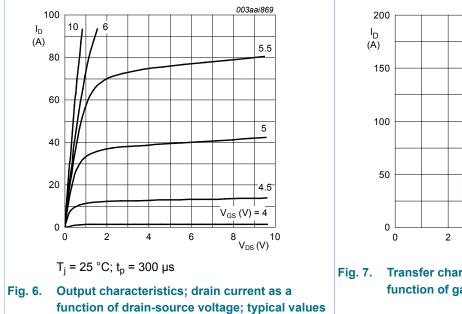
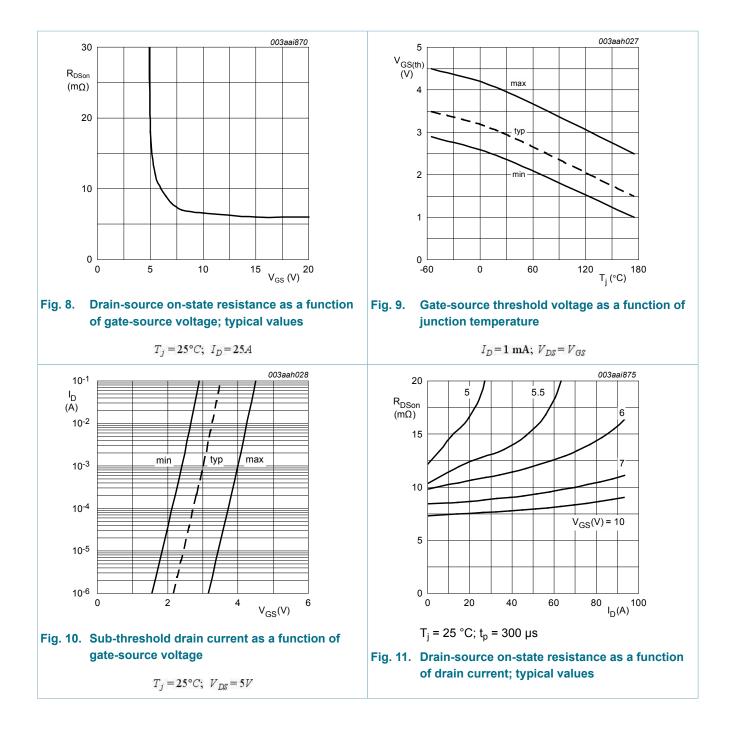


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$ 

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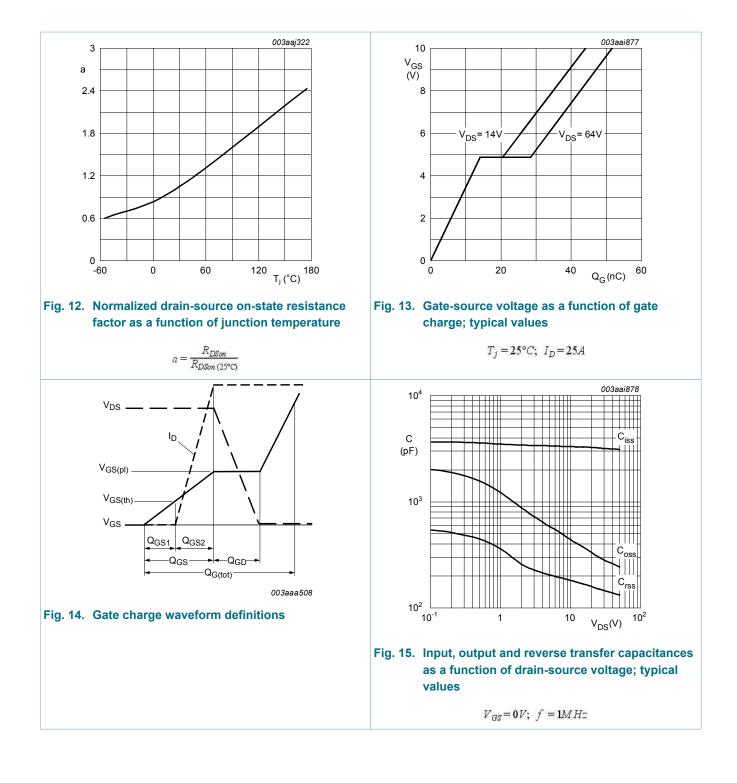
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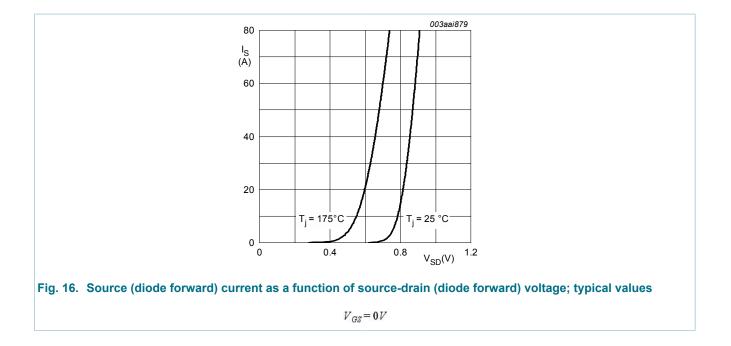
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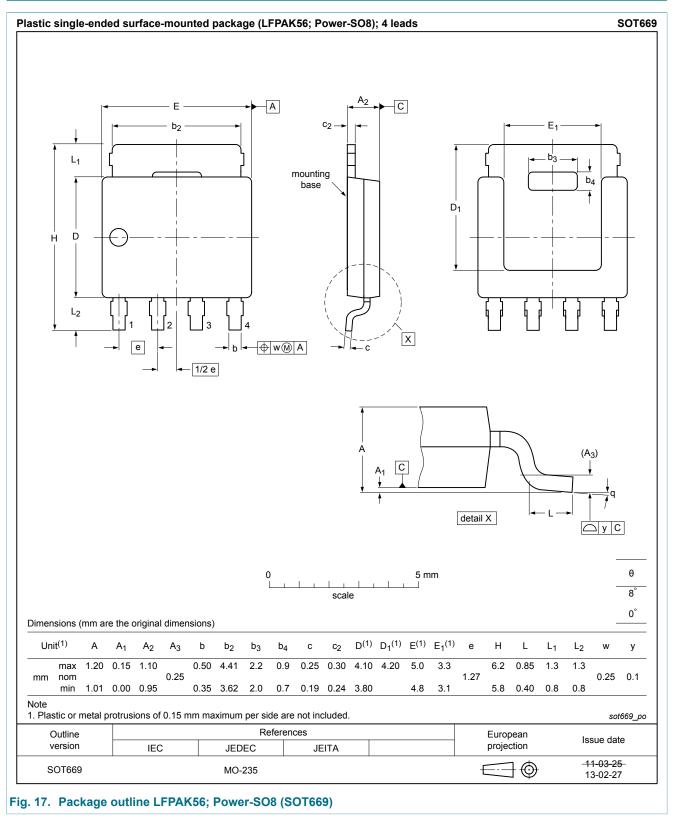
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## **11. Package outline**



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#### N-channel 80 V, 9.9 mΩ standard level MOSFET in LFPAK56

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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